

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D $T_C = +25^\circ C$
60V	27m Ω @ $V_{GS} = 10V$	22.6A
	30m Ω @ $V_{GS} = 6V$	21.5A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

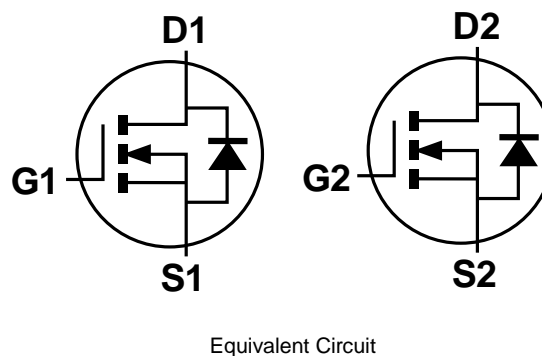
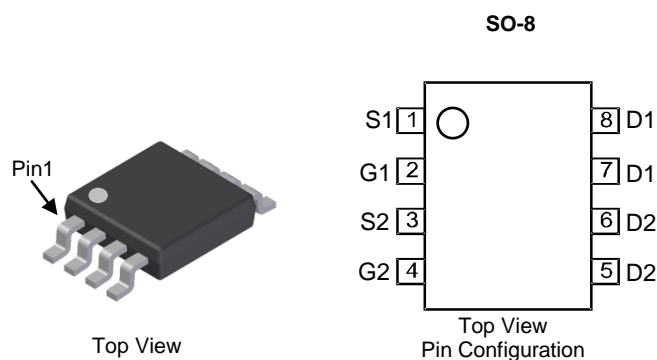
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low $R_{DS(ON)}$ – Minimizes Power Losses
- Low Q_g – Minimizes Switching Losses
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 $\text{\textcircled{E}}$
- Weight: 0.074 grams (Approximate)

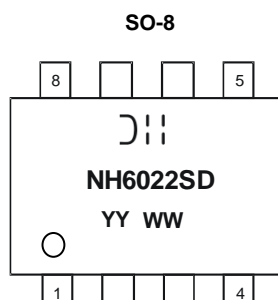


Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH6022SSD-13	SO-8	2,500 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



DII = Manufacturer's Marking
 NH6022SD = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 16 = 2016)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current V _{GS} = 10V (Note 6)	T _C = +25°C	22.6	A
	T _C = +100°C	16.0	A
	T _A = +25°C	7.1	A
	T _A = +70°C	5.9	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	45	A
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	2	A
Avalanche Current L=0.1mL (Note 7)	I _{AS}	22	A
Avalanche Energy L=0.1mL (Note 7)	E _{AS}	24	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	Steady State	104
		t < 10s	60
Total Power Dissipation (Note 6)	P _D	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	Steady State	74
		t < 10s	42
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	7.25	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	µA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	3.0	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	21	27	mΩ	V _{GS} = 10V, I _D = 5A
			24	30		V _{GS} = 6V, I _D = 5A
Diode Forward Voltage	V _{SD}	—	0.8	1.2	V	V _{GS} = 0V, I _S = 1.7A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iSS}	—	2127	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	86	—	pF	
Reverse Transfer Capacitance	C _{rSS}	—	54	—	pF	
Gate Resistance	R _g	—	2.0	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge at (V _{GS} = 10V)	Q _g	—	32	—	nC	V _{DS} = 30V, I _D = 6A
Total Gate Charge at (V _{GS} = 4.5V)	Q _g	—	14	—	nC	
Gate-Source Charge	Q _{gs}	—	7	—	nC	
Gate-Drain Charge	Q _{gd}	—	4	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	5.4	—	ns	V _{GS} = 10V, V _{DS} = 30V, R _g = 6Ω, I _D = 1A
Turn-On Rise Time	t _R	—	4.4	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	30.4	—	ns	
Turn-Off Fall Time	t _F	—	8.4	—	ns	
Body Diode Reverse Recovery Time	t _{RR}	—	18.1	—	ns	I _F = 1.7A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	—	12.5	—	nC	I _F = 1.7A, di/dt = 100A/µs

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
 7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.

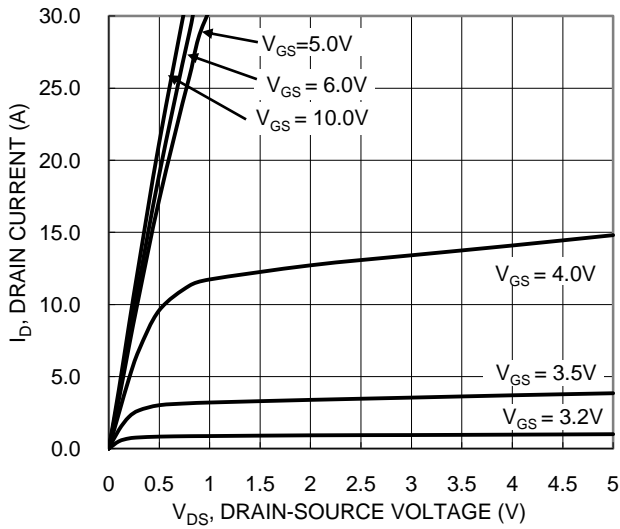


Figure 1. Typical Output Characteristic

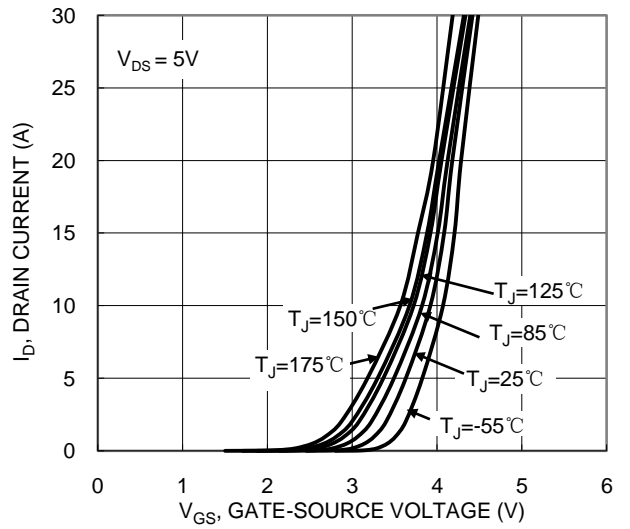


Figure 2. Typical Transfer Characteristic

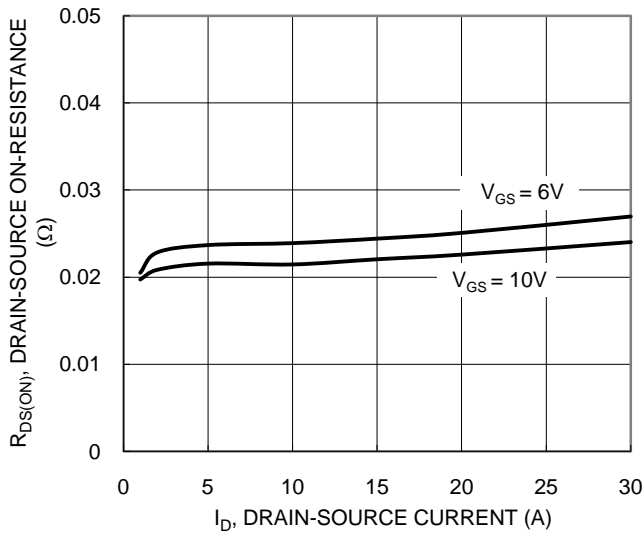


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

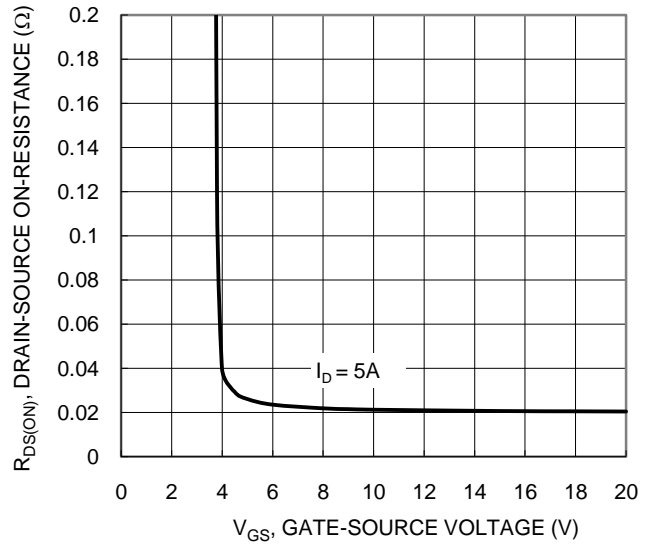


Figure 4. Typical Transfer Characteristic

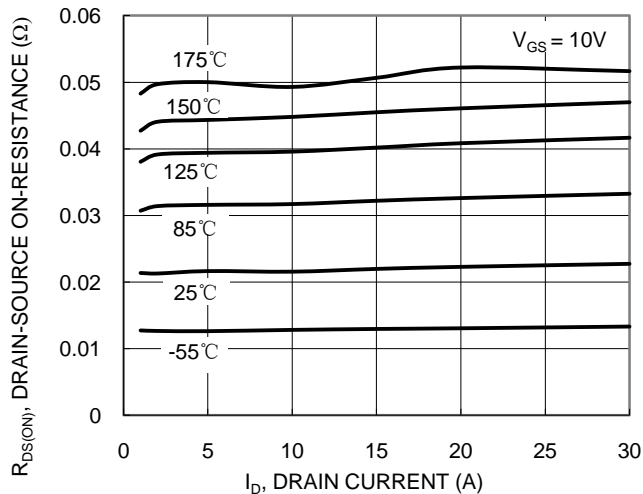


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

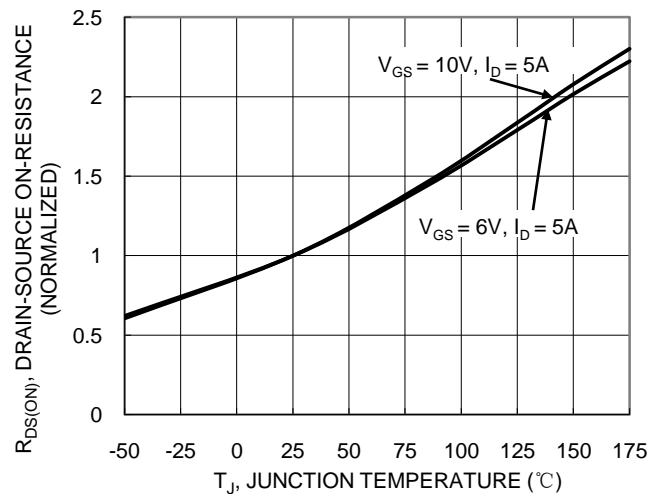


Figure 6. On-Resistance Variation with Junction Temperature

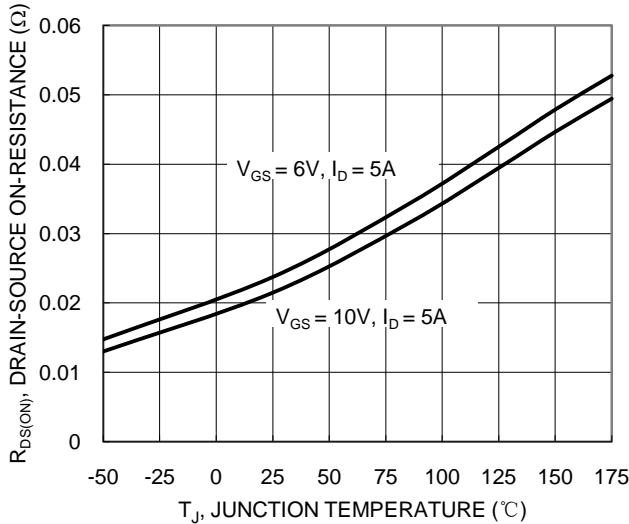


Figure 7. On-Resistance Variation with Junction Temperature

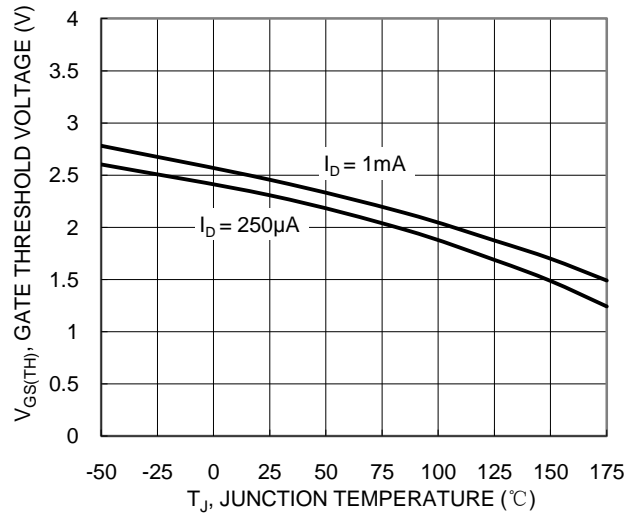


Figure 8. Gate Threshold Variation vs. Junction Temperature

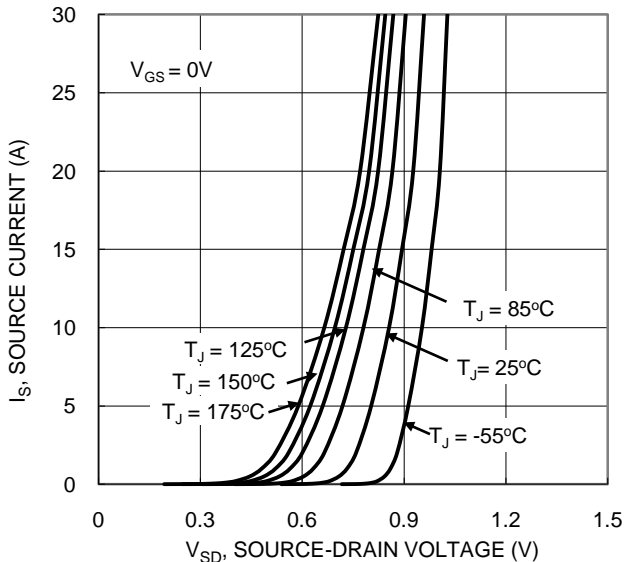


Figure 9. Diode Forward Voltage vs. Current

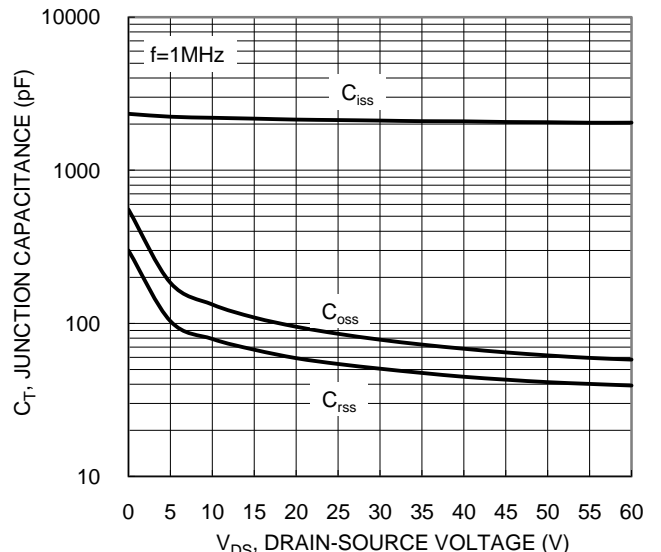


Figure 10. Typical Junction Capacitance

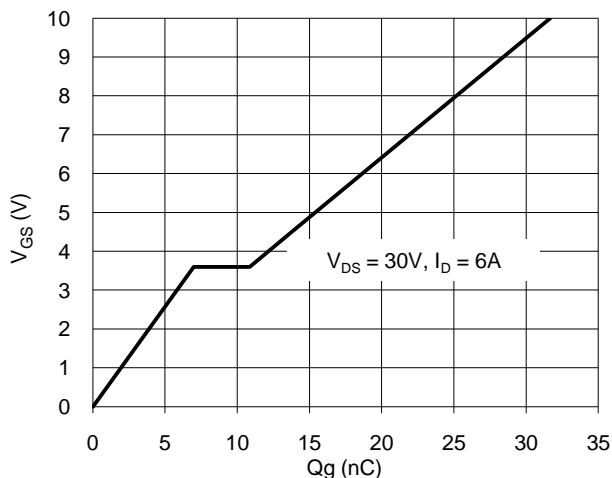


Figure 11. Gate Charge

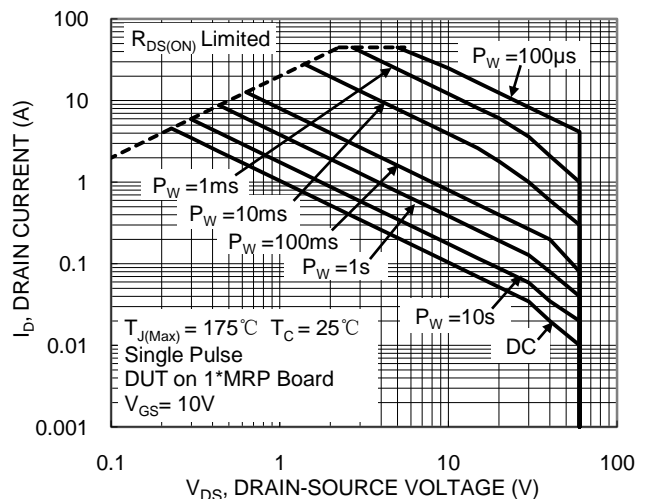


Figure 12. SOA, Safe Operation Area

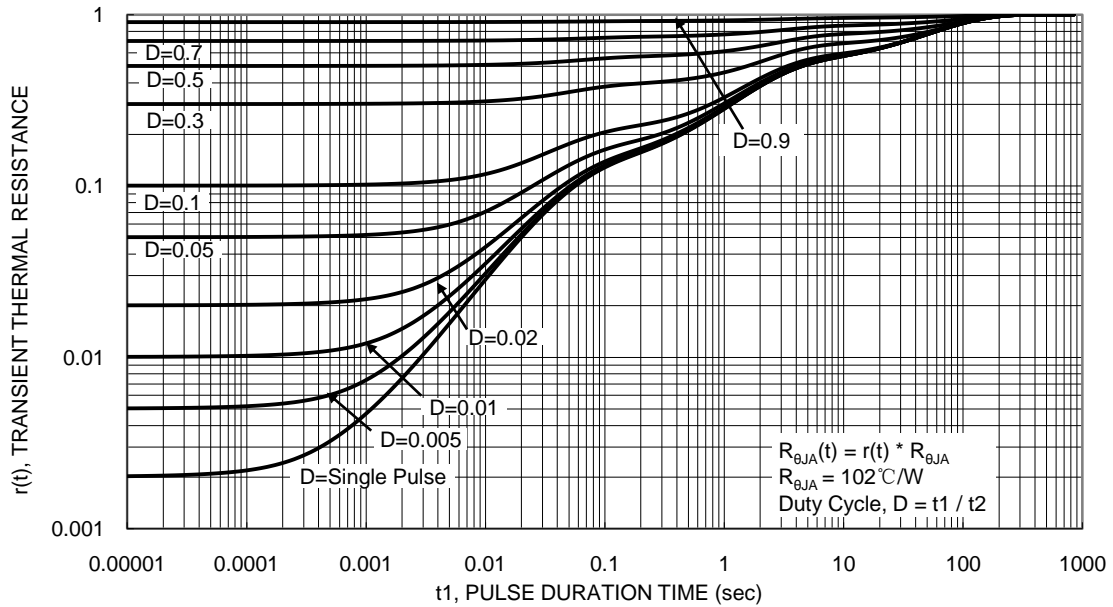
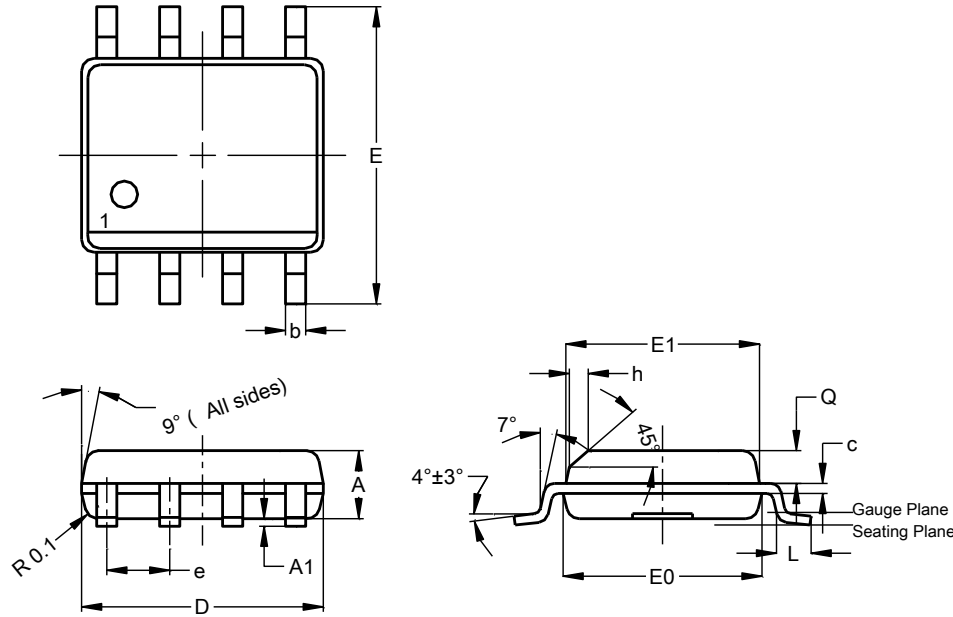


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8

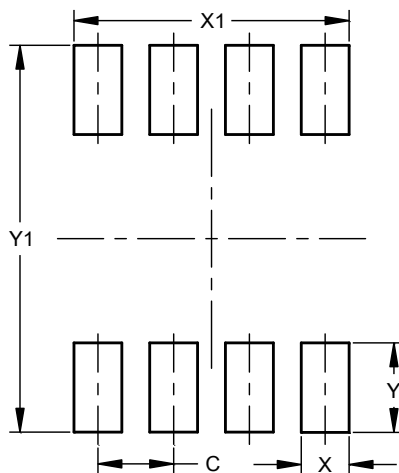


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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